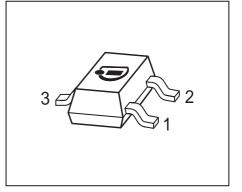


**BF775** 

## **NPN Silicon RF Transistor**

- Especially suitable for TV-Sat and UHF tuners
- Pb-free (RoHS compliant) package<sup>1)</sup>
- Qualified according AEC Q101





ESD (Electrostatic discharge) sensitive device, observe handling precaution!

Туре	Marking	Pin Configuration			Package
BF775	LOs	1 = B	2 = E	3 = C	SOT23

#### **Maximum Ratings**

Parameter	Symbol	Value	Unit	
Collector-emitter voltage	V <sub>CEO</sub>	15	V	
Collector-emitter voltage	V <sub>CES</sub>	20		
Collector-base voltage	V <sub>CBO</sub>	20		
Emitter-base voltage	V <sub>EBO</sub>	2.5		
Collector current	I <sub>C</sub>	45	mA	
Base current	I <sub>B</sub>	4		
Total power dissipation <sup>2)</sup>	P <sub>tot</sub>	280	mW	
$T_{\rm S} \le 48^{\circ}{\rm C}$				
Junction temperature	Ti	150	°C	
Ambient temperature	T <sub>A</sub>	-65 150		
Storage temperature	T <sub>stg</sub>	-65 150		

### Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point <sup>3)</sup>	R <sub>thJS</sub>	≤ 365	K/W

<sup>1</sup>Pb-containing package may be available upon special request

 $^2 T_{S}$  is measured on the collector lead at the soldering point to the pcb

<sup>3</sup>For calculation of  $R_{\rm thJA}$  please refer to Application Note Thermal Resistance



Parameter	Symbol	Values			Unit
			typ.	max.	]
DC Characteristics					
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	15	-	-	V
$I_{\rm C} = 1  {\rm mA},  I_{\rm B} = 0$					
Collector-emitter cutoff current	I <sub>CES</sub>	-	-	10	μA
$V_{\rm CE} = 20  \rm V,  V_{\rm BE} = 0$					
Collector-base cutoff current	I <sub>CBO</sub>	-	-	100	nA
$V_{\rm CB} = 10  \rm V, \ I_{\rm E} = 0$					
Emitter-base cutoff current	I <sub>EBO</sub>	-	-	100	μA
$V_{\rm EB} = 2.5 \text{ V}, I_{\rm C} = 0$					
DC current gain-	h <sub>FE</sub>	70	100	140	-
$I_{\rm C}$ = 15 mA, $V_{\rm CE}$ = 8 V, pulse measured					

# **Electrical Characteristics** at $T_A = 25^{\circ}C$ , unless otherwise specified

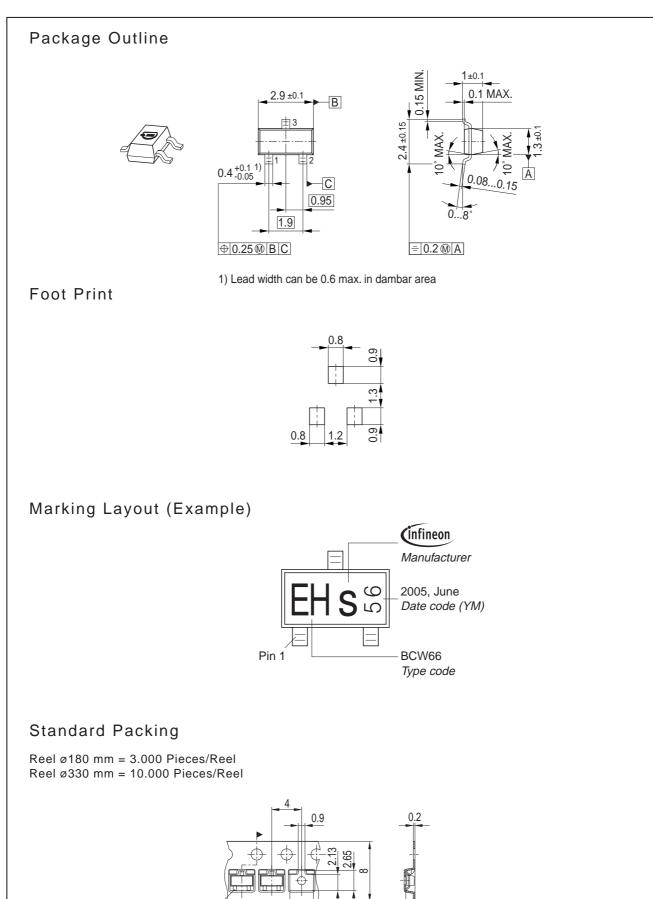


Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics (verified by random samp	ling)				-
Transition frequency	f <sub>T</sub>	3.5	5	-	GHz
<i>I</i> <sub>C</sub> = 15 mA, <i>V</i> <sub>CE</sub> = 8 V, <i>f</i> = 500 MHz					
Collector-base capacitance	C <sub>cb</sub>	-	0.39	0.55	pF
$V_{\rm CB} = 10 \text{ V}, \ f = 1 \text{ MHz}, \ V_{\rm BE} = 0 ,$					
emitter grounded					
Collector emitter capacitance	C <sub>ce</sub>	-	0.23	-	
$V_{CE} = 10 \text{ V}, f = 1 \text{ MHz}, V_{BE} = 0$ ,					
base grounded					
Emitter-base capacitance	C <sub>eb</sub>	-	0.64	-	
$V_{\text{EB}} = 0.5 \text{ V}, f = 1 \text{ MHz}, V_{\text{CB}} = 0$ ,					
collector grounded					
Noise figure	F				dB
$I_{\rm C}$ = 2 mA, $V_{\rm CE}$ = 6 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$ ,					
<i>f</i> = 900 MHz		-	1.4	-	
<i>f</i> = 1.8 GHz		-	2	-	
Power gain, maximum available <sup>1)</sup>	G <sub>ma</sub>				
$I_{\rm C}$ = 15 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$ ,					
$Z_{\rm L} = Z_{\rm Lopt}, f = 900 \text{ MHz}$		-	16	-	
f = 1.8  GHz		-	10.5	-	
Transducer gain	S <sub>21e</sub>   <sup>2</sup>				dB
$I_{\rm C}$ = 15 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm L}$ = 50 $\Omega$ ,					
<i>f</i> = 900 MHz		-	13	-	
<i>f</i> = 1.8 GHz		-	7.5	-	

<b>Electrical Characteristics</b> at $T_A = 25^{\circ}$ C, unless other	erwise specified

 ${}^{1}\mathrm{G}_{\mathrm{ma}} = |\mathrm{S}_{21}/\mathrm{S}_{12}| \; (\mathrm{k} \cdot (\mathrm{k}^{2} \cdot 1)^{1/2})$ 





1.15

3.15

Pin 1



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